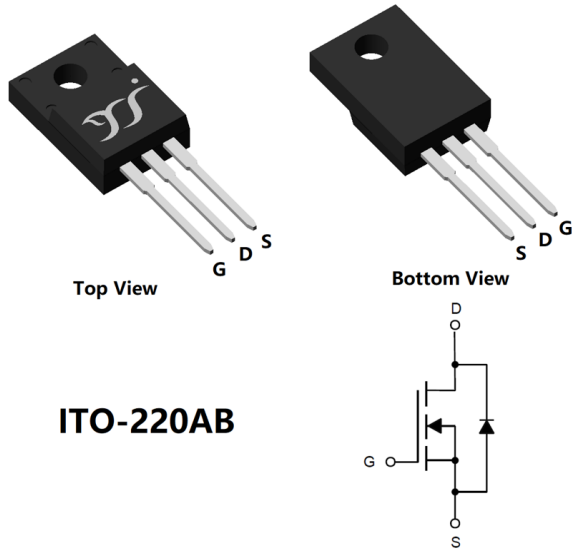


N-Channel Enhancement Mode Field Effect Transistor



ITO-220AB

Product Summary

- V_{DS} 150V
- I_D 30A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<24m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=6V$) $<26m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Excellent stability and uniformity
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Units
Drain-source Voltage		V_{DS}	150	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	7	A
	$T_A=100^\circ C$		4	
	$T_C=25^\circ C$		30	
	$T_C=100^\circ C$		19	
Pulsed Drain Current ^A		I_{DM}	120	A
Avalanche energy ^B		EAS	285	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		50	
	$T_C=100^\circ C$		20	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	2	2.5	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJF30G15H	B1	YJF30G15H	50	/	5000	Tube



YJF30G15H

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1	μA
		V _{DS} =150V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.9	4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	18	24	mΩ
		V _{GS} =6V, I _D =20A	-	20	26	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	-	1.2	V
Gate resistance	R _G	f=1MHz	-	1	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	30	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =75V, V _{GS} =0V, f=1MHz	-	2530	-	pF
Output Capacitance	C _{oss}		-	210	-	
Reverse Transfer Capacitance	C _{rss}		-	8	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =75V, I _D =20A	-	40	-	nC
Gate-Source Charge	Q _{gs}		-	10	-	
Gate-Drain Charge	Q _{gd}		-	11	-	
Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/us	-	215	-	nC
Reverse Recovery Time	t _{rr}		-	93	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =75V, I _D =20A R _{GEN} =4.5Ω	-	16	-	ns
Turn-on Rise Time	t _r		-	14	-	
Turn-off Delay Time	t _{D(off)}		-	30	-	
Turn-off fall Time	t _f		-	13	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=100V, V_G=10V, R_G=25Ω, L=2mH, I_{AS}=16.9A.

C. P_q is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



YJF30G15H

Typical Electrical and Thermal Characteristics Diagrams

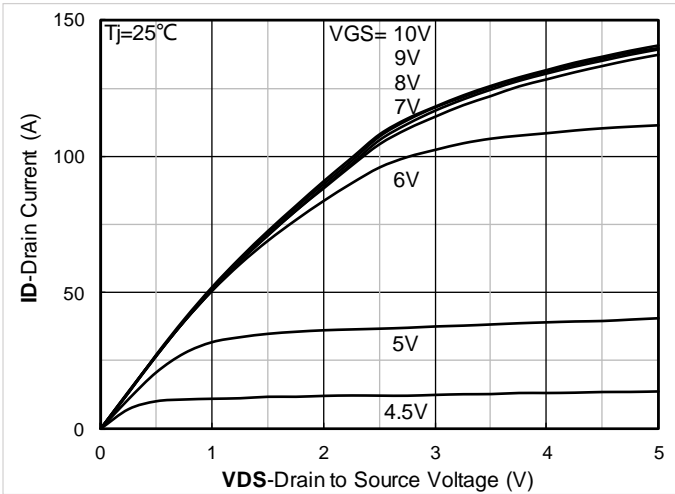


Figure 1. Output Characteristics

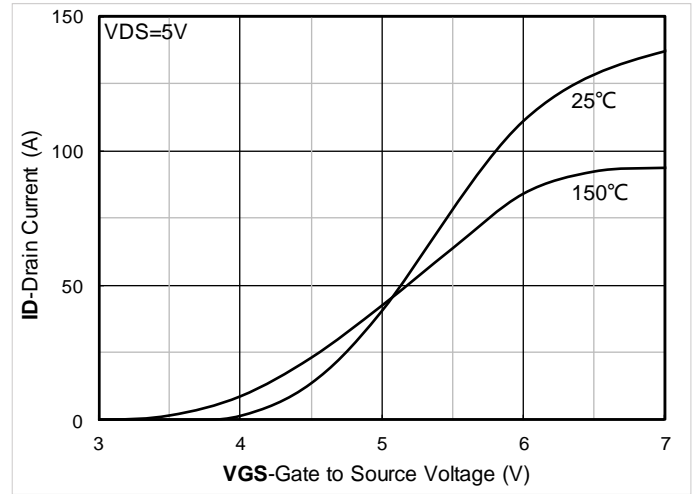


Figure 2. Transfer Characteristics

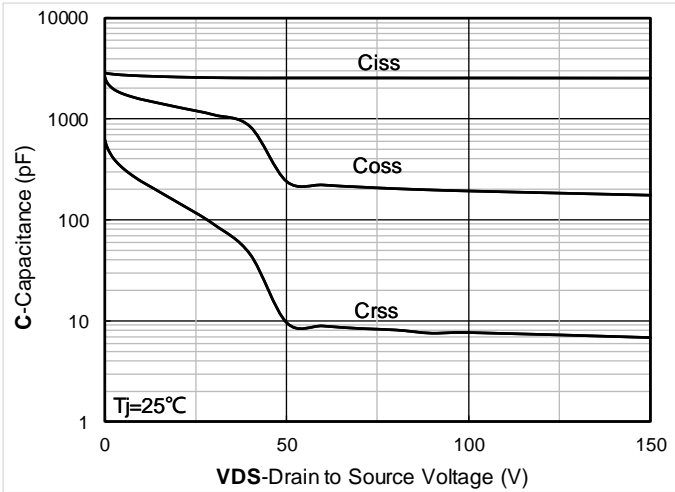


Figure 3. Capacitance Characteristics

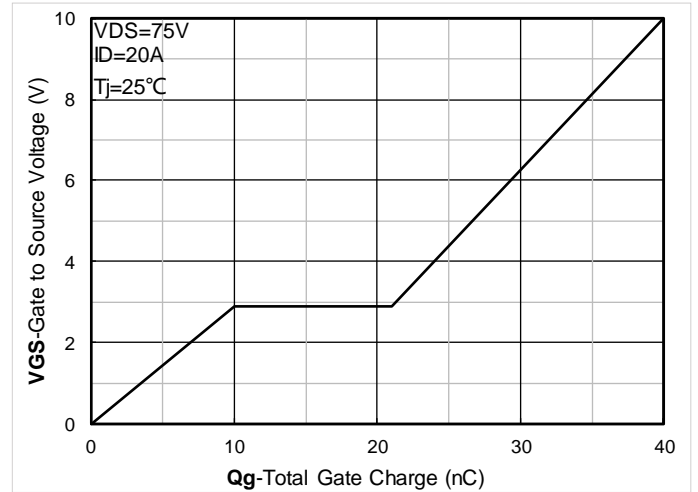


Figure 4.



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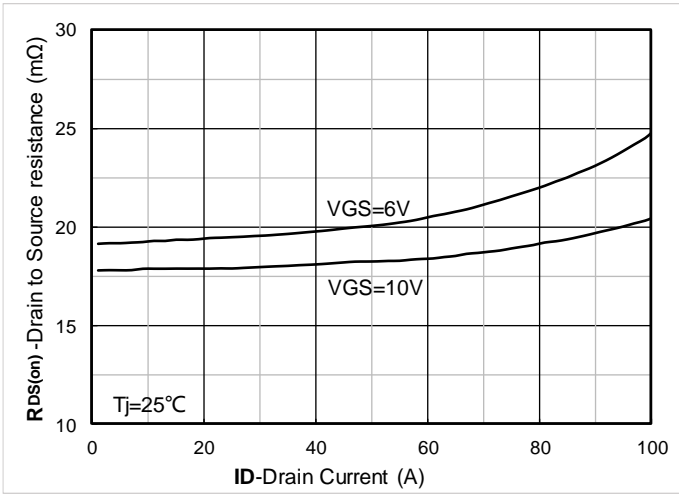


Figure 7. $R_{DS(on)}$ VS Drain Current

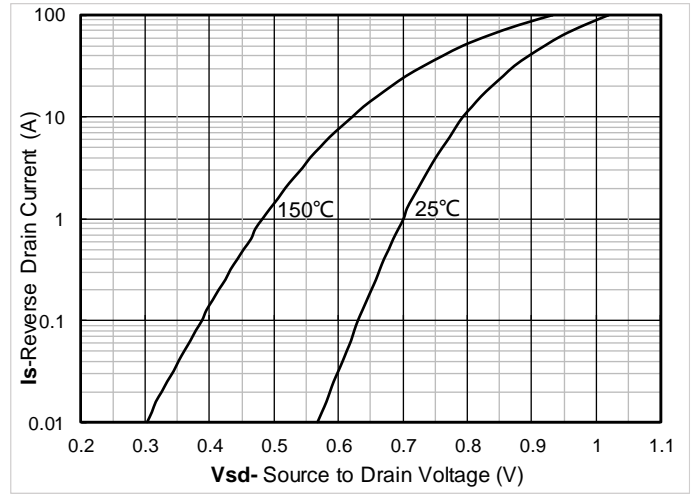


Figure 8. Forward characteristics of reverse diode

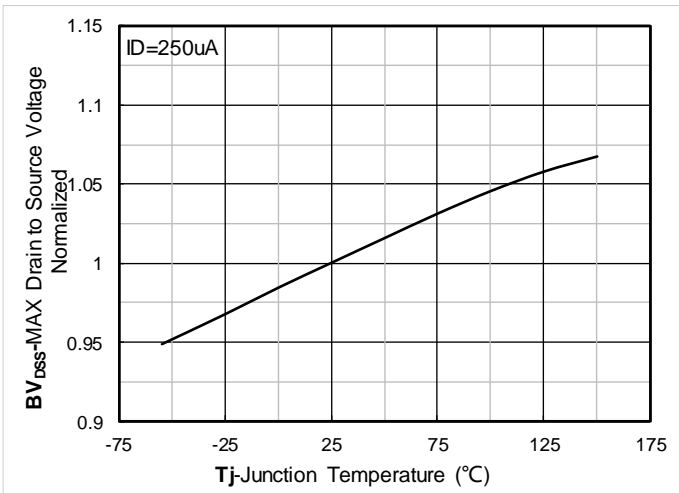


Figure 9. Normalized breakdown voltage

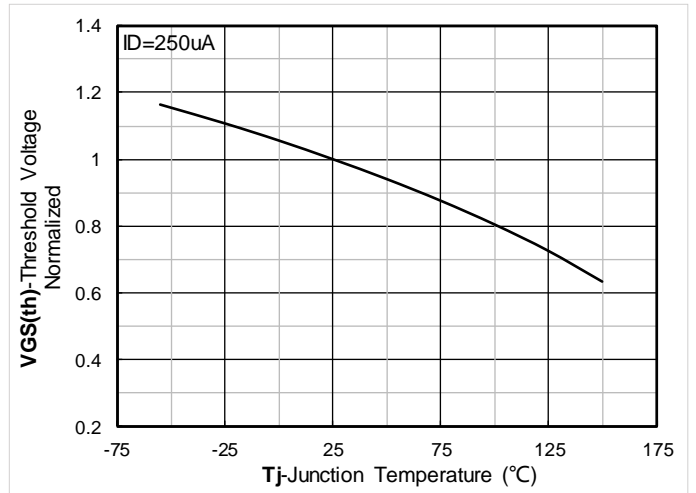


Figure 10. Normalized Threshold voltage

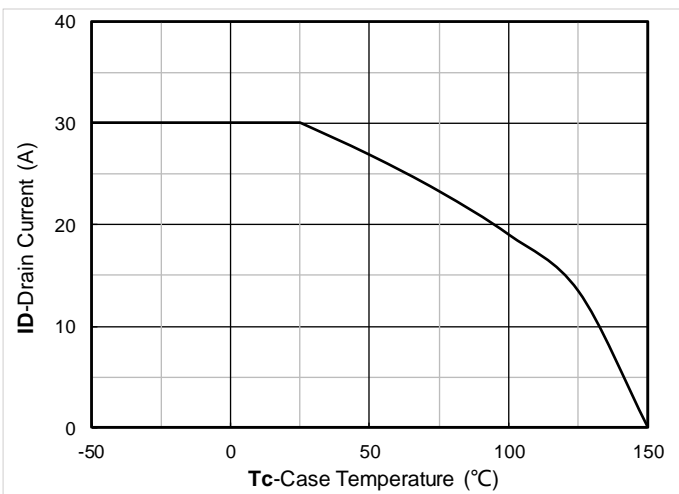


Figure 11. Current dissipation

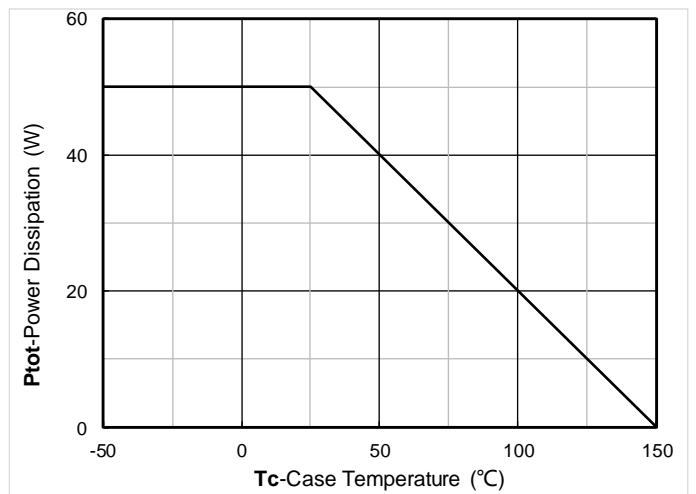


Figure 12. Power dissipation

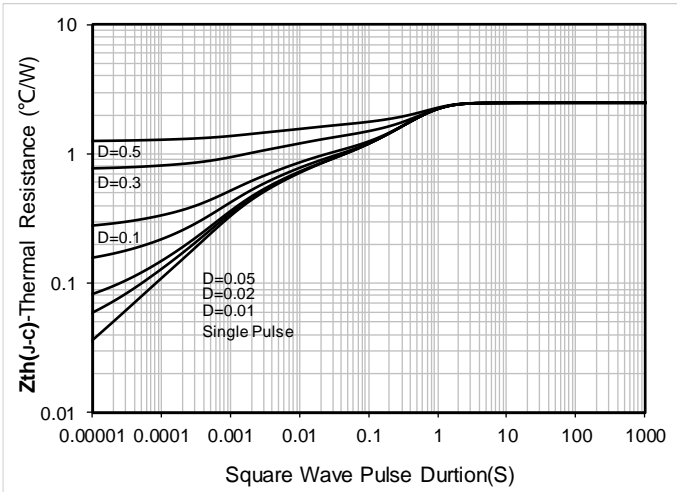


Figure 13. Maximum Transient Thermal Impedance

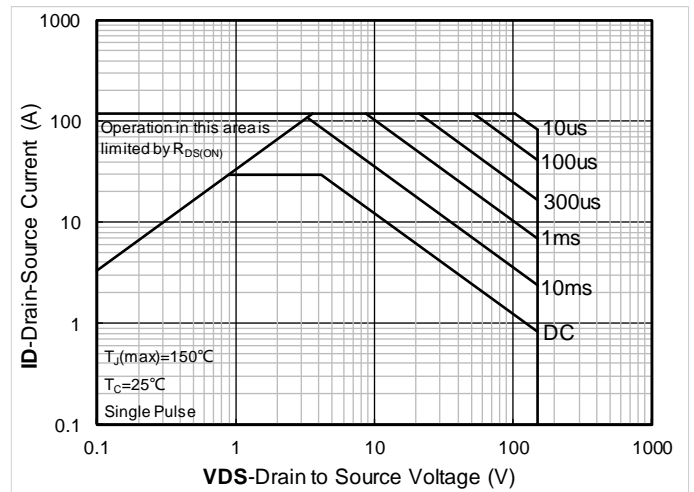


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

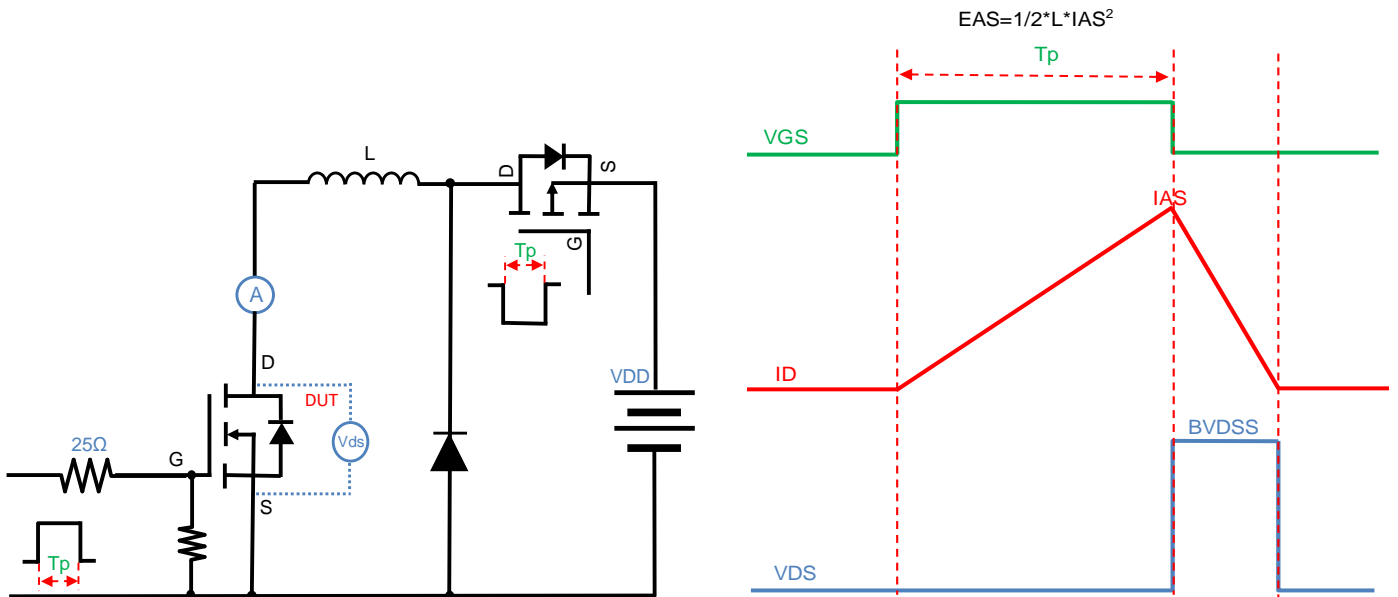


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Figure B. Gate Charge Test Circuit & Waveform



Figure C. Resistive Switching Test Circuit & Waveform

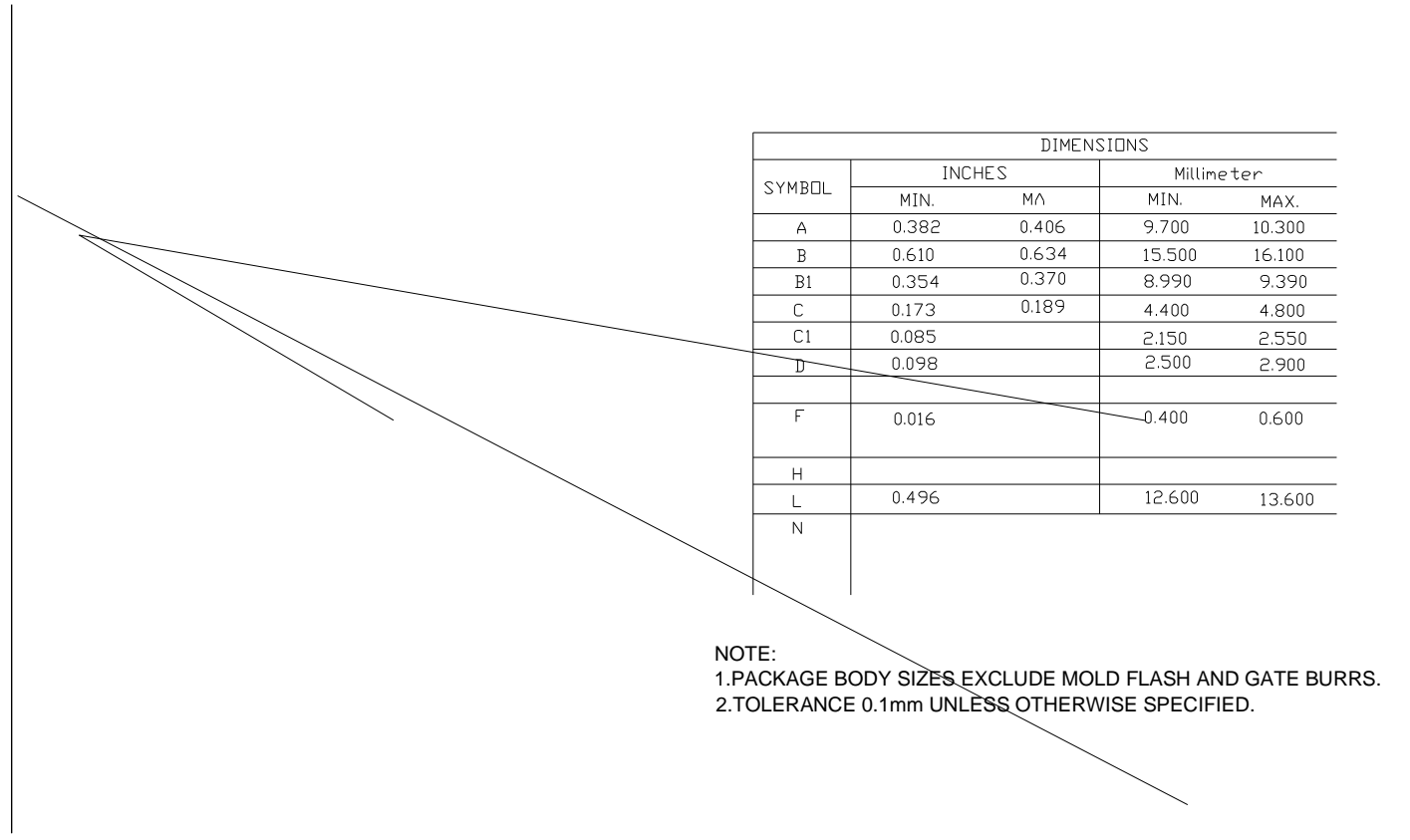


Figure D. Diode Recovery Test Circuit & Waveform



YJF30G15H

■ ITO-220AB-B Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.382	0.406	9.700	10.300
B	0.610	0.634	15.500	16.100
B1	0.354	0.370	8.990	9.390
C	0.173	0.189	4.400	4.800
C1	0.085		2.150	2.550
D	0.098		2.500	2.900
F	0.016		0.400	0.600
H				
L	0.496		12.600	13.600
N				

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

